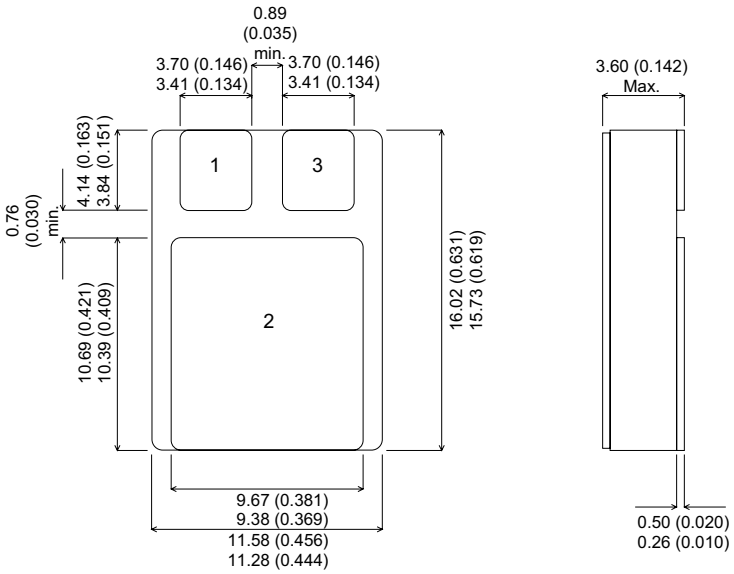
IRF9130SMD

MECHANICAL DATA
Dimensions in mm (inches)



SMD 1

Pad 1 – Gate Pad 2 – Drain Pad 3 – Source

(also available as IRFN9130SMD with Gate and Source reversed)

P–CHANNEL POWER MOSFET FOR HI–REL APPLICATIONS

V_{DSS}	-100V
$I_{D(cont)}$	-8A
$R_{DS(on)}$	0.35Ω

FEATURES

- **HERMETICALLY SEALED**
- **SIMPLE DRIVE REQUIREMENTS**
- **LIGHTWEIGHT**
- **SCREENING OPTIONS AVAILABLE**
- **ALL LEADS ISOLATED FROM CASE**

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{GS}	Gate – Source Voltage	±20V
I_D	Continuous Drain Current @ T_{case} = 25°C	8A
I_D	Continuous Drain Current @ T_{case} = 100°C	5A
I_{DM}	Pulsed Drain Current	40A
P_D	Power Dissipation @ T_{case} = 25°C	45W
	Linear Derating Factor	0.36W/°C
T_J , T_{stg}	Operating and Storage Temperature Range	–55 to 150°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	2.8°C/W max.

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Prelim. 09/00

IRF9130SMD

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	V_{GS} = 0 I_D = 1mA	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I_D = 1mA		0.1		V/°C
$R_{DS(on)}$	Static Drain – Source On–State Resistance	V_{GS} = 10V I_D = 5A			0.35	Ω
		V_{GS} = 10V I_D = 8A			0.4	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250µA	2		4	V
g_{fs}	Forward Transconductance	V_{DS} ≥ 15V I_{DS} = 5A	3			S(℧)
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V_{DS} = 0.8BV_{DSS}			25	µA
		T_J = 125°C			250	
I_{GSS}	Forward Gate – Source Leakage	V_{GS} = 20V			100	nA
I_{GSS}	Reverse Gate – Source Leakage	V_{GS} = –20V			-100	
	DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	V_{GS} = 0		860		pF
C_{oss}	Output Capacitance	V_{DS} = 25V		350		
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		125		
Q_g	Total Gate Charge	V_{GS} = 10V I_D = 8A V_{DS} = 0.5BV_{DSS}	12.5		29	nC
Q_{gs}	Gate – Source Charge	I_D = 8A	1.0		6.3	nC
Q_{gd}	Gate – Drain (“Miller”) Charge	V_{DS} = 0.5BV_{DSS}	2		27	
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 50V I_D = 8A R_G = 7.5Ω			60	ns
t_r	Rise Time				140	
$t_{d(off)}$	Turn–Off Delay Time				140	
t_f	Fall Time				140	
	SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current				8	A
I_{SM}	Pulse Source Current				32	
V_{SD}	Diode Forward Voltage	I_S = 8A T_J = 25°C V_{GS} = 0			4.7	V
t_{rr}	Reverse Recovery Time	I_S = 8A T_J = 25°C			300	ns
Q_{rr}	Reverse Recovery Charge	d_i / d_t ≤ 100A/µs V_{DD} ≤ 50V			3	µC
	PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (from 6mm down drain lead pad to centre of die)			8.7		nH
L_S	Internal Source Inductance (from 6mm down source lead to centre of source bond pad)			8.7		